

## IN THE SPECIFICATION

5           Please amend the paragraph on page 3, lines 6 - 8, following  
the SUMMARY OF THE INVENTION heading as follows:

          The present invention provides a method of long-term low  
temperature annealing of semiconductor devices to form ohmic  
10   contact regions between a layer of wide band-gap semiconductor  
material and ~~spaced-apart~~ contact areas disposed thereon.

          Please amend the paragraph on page 5, line 19 through  
15   page 6, line 9, as follows:

          Contact layer 16, such as, for example, aluminum, zinc, nickel or other  
similar metal, is formed by, for example, sputtering, chemical vapor  
deposition, or other processes, over wide band-gap semiconductor material  
20   layer 14. Contact layer 16 and wide band-gap semiconductor material layer  
14 are in substantially continuous contact. As deposited and prior to  
annealing, contact layer 16 forms a rectifying or otherwise non-ohmic  
connection to wide band-gap semiconductor material layer 14. Contact layer  
16 is typically patterned and etched by known methods to expose desired  
25   portions of wide band-gap semiconductor material layer 14. Features (not  
shown) are then etched in the wide band-gap semiconductor material layer 14  
using known methods, and to form functional circuit structures and thereby a  
functional semiconductor device 10. The portion or portions of contact layer  
16 that remain after etching define one or more contact areas 20 (Fig. 2).

Please amend the paragraph on page 7, line 17 through  
5 page 8 line 5, as follows:

Referring now to Fig. [[2]] 4, the current vs. voltage curves obtained  
between two spaced-apart contact regions 22 formed as a result of various  
annealing parameters are shown. In the exemplary embodiment of the  
10 method of the present invention, a plurality of devices 10 were formed.  
Devices 10 included nickel (Ni) contacts 20 having an approximate thickness  
of from 2400 to 2600 Angstroms. The contacts 20 were deposited via  
electron beam evaporation at a background pressure of approximately  $1 \times 10^{-7}$   
Torr onto a wide band-gap semiconductor material layer 14 of 4H silicon  
15 carbide (SiC). The devices 10 were then divided into several groups of one or  
more devices. Each group was then subjected to respective annealing  
processes of correspondingly different temperatures and/or durations.

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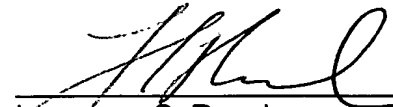
Please amend the paragraph on page 11, lines 18 – 21, as  
follows:

In the embodiment shown, the wide band-gap  
25 semiconductor material is configured as 4H silicon carbide.  
However, it is to be understood that the method of the present  
invention is equally applicable to different poly-types of silicon  
carbide, such as, for example, ~~6H-SiC and 3C-SiC~~. 6H-SiC and 3C-  
SiC.

Respectfully submitted,

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Date

  
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